

# **A 1.29GHz 251.16fJ 6-bit Absolute-Value Detector**

**Dennis Zang  
August Greer  
Grant Roberts**



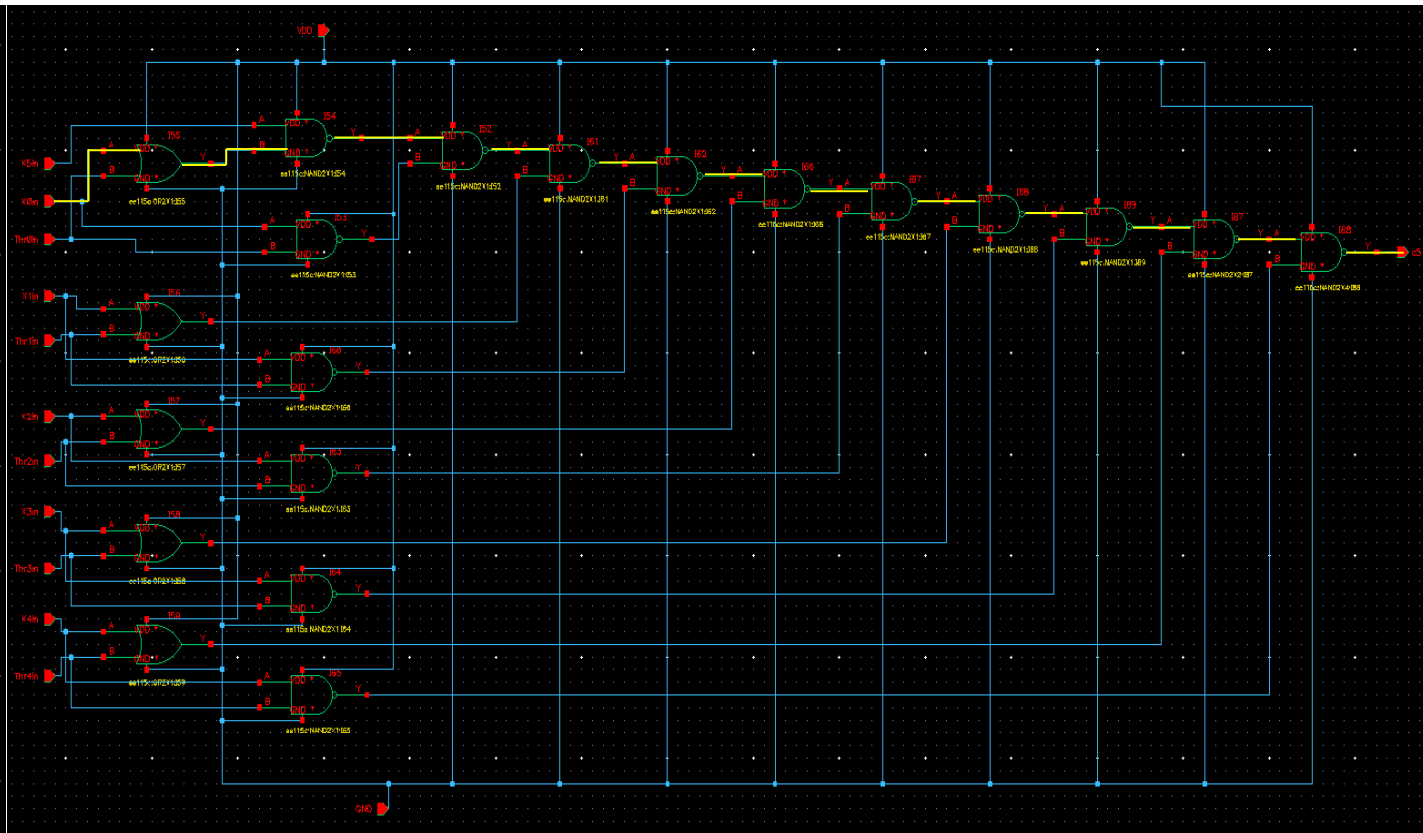
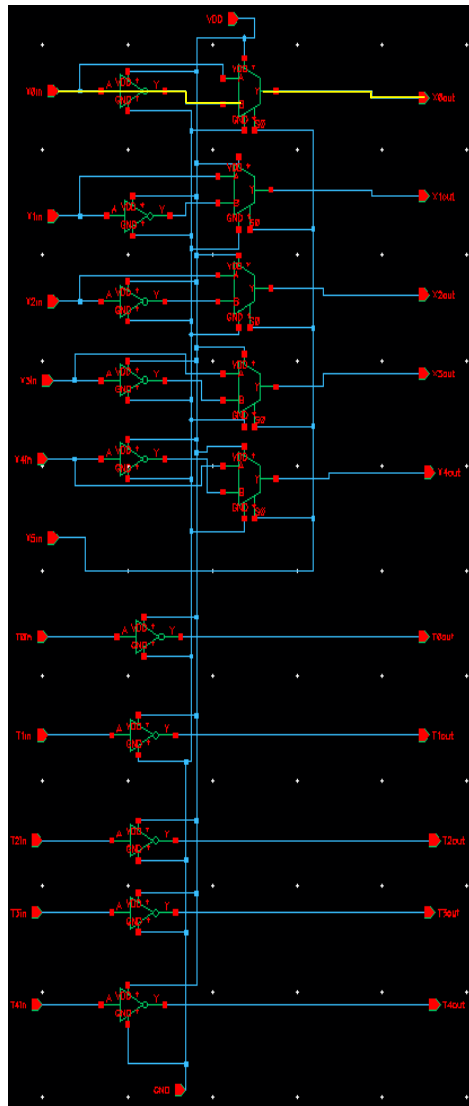
# Design Summary

- ◆ **Circuit topology:** (Multiplexors/Invertors) followed by a Carry-Propagate Comparator
- ◆ **Circuit Style:** all static CMOS
- ◆ **C) WHY:**
  - use of carry-propagate as comparator reduces the total number of gates and transistors, making better use of area and using less power (compared to the normal comparator)
  - carry-propagate comparator allows for regular design (repeated use of NAND gates)

Delay	Layout size	Energy	Verification
Sch. $t_p = 772.95\text{ps}$	$X = 15.815\mu\text{m}$ , $Y = 26.965\mu\text{m}$	Sch. $E = 187.22\text{fJ}$	Func: Y
Lay. $t_p = 749.95\text{ps}$	$A = 426.45\mu\text{m}^2$	Lay. $E = 251.16\text{fJ}$	DRC: Y
Critical Input = $X_0$	$AR = 1.7$	Lay. $V_{DD} = 0.69\text{V}$	LVS: Y

\*(assuming Vdd is fully optimized for a delay of ~775ps)

# Critical Path Analysis



$$T_{crit} = T_{INV} + T_{MUX} + T_{OR} + 10T_{NAND}$$

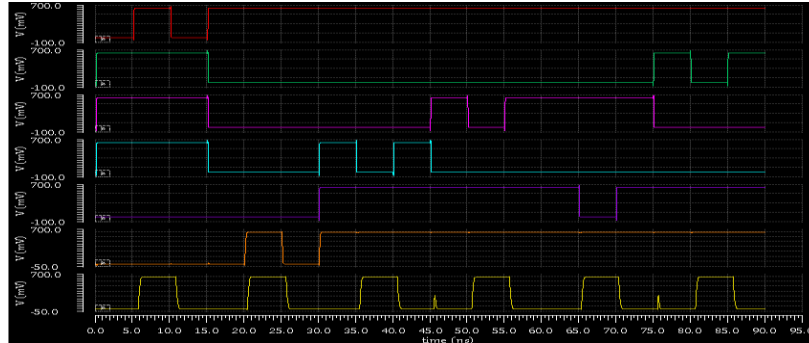
# Design Optimization

---

- ◆ Gate level critical path:
  - propagation from  $X_0$  (if it changes) to  $C_5$  (out)
  - majority of delay come from the chain of NAND gates
- ◆ MOS detail of gates, sizing, and optimization strategy:
  - mainly used standard cells from gsclib090
  - optimization strategies:
    - use of NANDs over NORs
      - (however, standard cells have same logical effort)
      - (lower  $T_{LH}$  than  $T_{HL}$ , and less energy in testbench)
    - buffering electrical fanout over last few gates
      - (experimented and found it best to size last 2 NANDs x2 and x4)
  - note: if threshold were to change frequently, then power consumption would increase due to unconditional inversion of the threshold

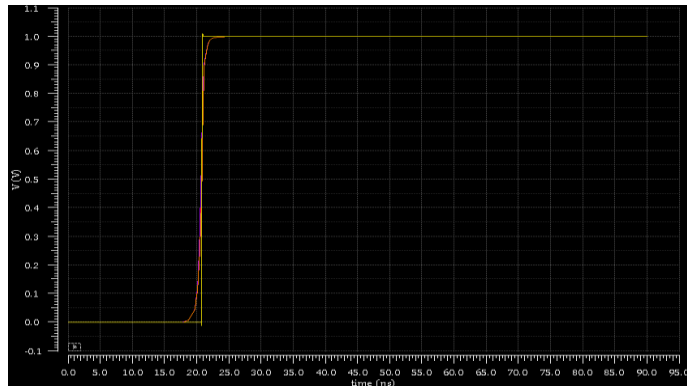
# Functionality Check

## ◆ Functionality (testbench)



## ◆ Worst-Case Delays ( $V_{dd} = 1$ )

( $T_{LH}$ )



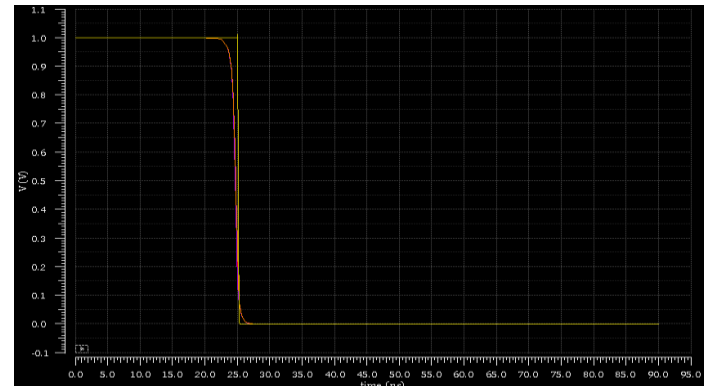
(X: 000000→111111)

(T = 000000)

(delay = 418ns)

(Note: because of the use of NAND gates,  $T_{LH}$  is less than  $T_{HL}$ )

( $T_{HL}$ )



(X: 111111→000000)

(T = 000000)

(delay = 458ns)

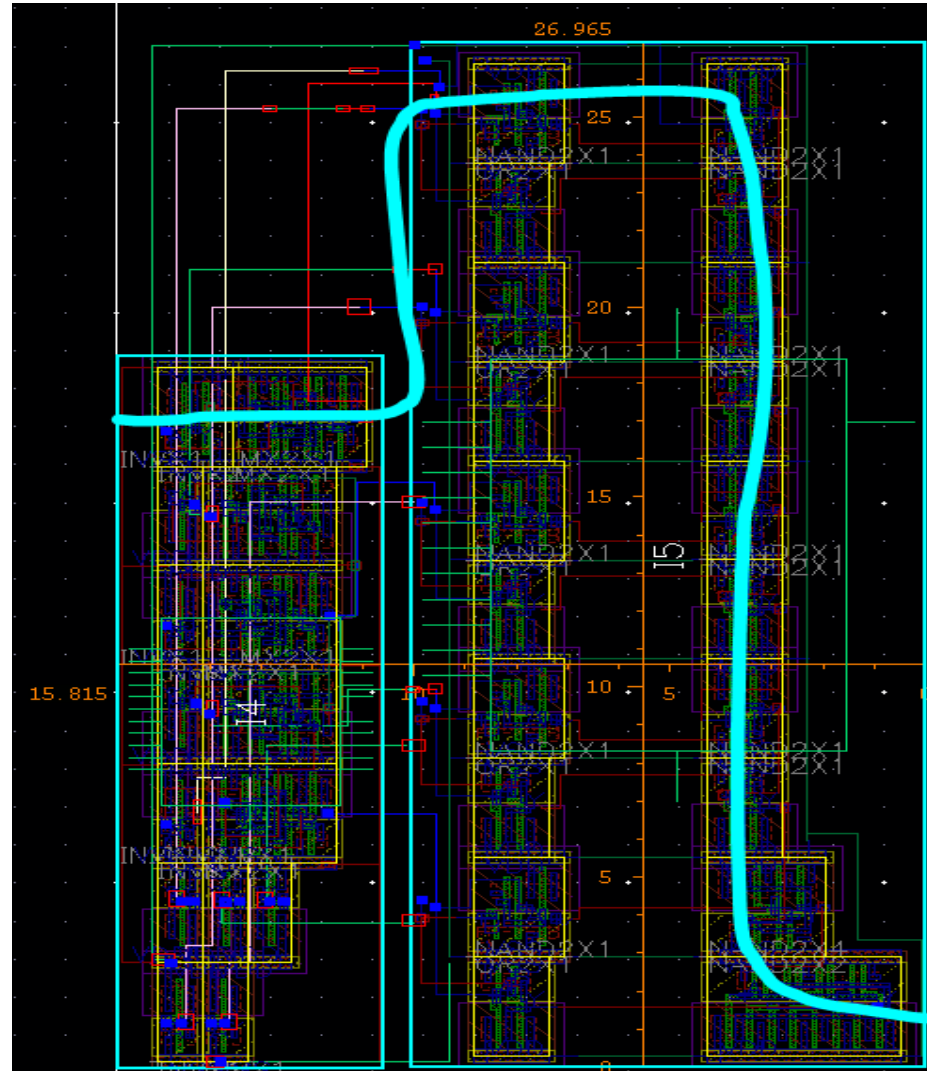
# Absolute-Value Detector Layout

Size:  $X = 26.965\mu\text{m}$   
 $Y = 15.815\mu\text{m}$

Area:  $426.45\mu\text{m}^2$

Aspect Ratio: 1.7

Density: 60%



# Discussion

---

## ◆ Most Important Features of Our Design:

- Sizing of last few logic gates to better buffer the electrical fanout
- Highly regular use of NAND gates in comparator
- Minimal use of non-(inverter/NAND/NOR) logic gates to minimize number of transistors, power, and area in layout

## ◆ Potential Improvements:

- Resizing gates  
(just halving the gate sizes cut down the energy by  $\sim 20\text{fJ}$ )
- Redo the layout of the comparator  
(much wasted space)
- Try to redesign the logic so that we can remove the invertors in the first stage  
(not much energy consumption since threshold has low switching frequency)  
(NOR-implemented comparator has higher energy consumption in current testbench)  
(would save some area for the layout by removing inverter logic gates)